Listing of the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application. Claims 38 and 52 are amended as follows:

1-37. (Cancelled)

38. (Currently Amended) An in-process substrate structure including a plurality of contact regions and a plurality of non-contact regions adjacent the contact regions on a surface of the substrate, the in-process substrate structure comprising:

a selectively formed contact epitaxially grown on each contact region, each contact being isolated from contacts on adjacent contact regions, each contact having a curved upper surface intersected by two sidewall surfaces, the two sidewall surfaces being substantially perpendicular to the surface of the substrate ~~and having a first surface exposed to electromagnetic radiation during formation to a greater extent than a second surface of the contact~~.

39-44. (Cancelled)

45. (Previously presented) The substrate of claim 38 wherein the non-contact regions adjacent to the contact region comprise isolation oxide regions.

46. (Previously presented) The substrate of claim 38 wherein the substrate comprises silicon.

47. (Previously presented) The substrate of claim 38 wherein the substrate comprises gallium arsenide.

48. (Previously presented) The substrate of claim 38 wherein the substrate comprises silicon germanium.

49. (Previously presented) The substrate of claim 38 wherein the contact comprises silicon.

50. (Previously presented) The substrate of claim 38 wherein the contact comprises gallium arsenide.

51. (Previously presented) The substrate of claim 38 wherein the contact comprises silicon germanium.

52. (Currently Amended) An in-process semiconductor structure, comprising:

a substrate;

a plurality of active regions;

a plurality of isolation regions adjacent the active regions, each isolation region being positioned between adjacent active regions to isolate adjacent active regions; and

at least one selectively formed contact ~~region~~ epitaxially grown on each active region, each selectively formed contact ~~region~~ being isolated from contacts on adjacent active regions, each selectively formed contact having a curved upper surface intersected by two sidewall surfaces, the two sidewall surfaces being substantially perpendicular to an upper surface of the active region ~~and having a first surface exposed to electromagnetic radiation during formation to a greater extent than a second surface of the contact~~.

53. (Previously presented) The in-process semiconductor structure of claim 52 wherein each isolation region comprises a field oxide region.

54. (Previously presented) The in-process semiconductor of claim 53 wherein the substrate comprises silicon.

55. (Previously presented) The in-process semiconductor of claim 53 wherein the substrate comprises gallium arsenide.

56. (Previously presented) The in-process semiconductor of claim 53 wherein the substrate comprises silicon germanium.

57. (Previously presented) The in-process semiconductor of claim 53 wherein each contact comprises selective epitaxial growth silicon.

58. (Previously presented) The in-process semiconductor of claim 53 wherein at least some of the contacts comprise gallium arsenide.

59. (Previously presented) The in-process semiconductor of claim 53 wherein at least some of the contacts comprise silicon germanium.

60. (Previously presented) The substrate of claim 38 wherein the electromagnetic radiation comprises collimated electromagnetic radiation.

61. (Previously presented) The in-process semiconductor of claim 53 wherein the electromagnetic radiation comprises collimated electromagnetic radiation.